



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



IPD series for Automotive

8ch Low-side switch

BD8LB600FS-C

Features

- Monolithic power IC that has a built-in control part (CMOS) and a power MOS FET on 1chip
- 8ch Low-side switch for driving resistive, inductive, capacitive load
- 16bit Serial peripheral interface(SPI) for diagnostics and control
- Built-in Open Load Detection circuit in output-off state
- Built-in Self restart Over Current Protection circuit (OCP)
- Built-in Over Voltage Protection for Output circuit
- Built-in Self restart Over Heating Protection circuit (TSD)
- Low On resistance of $R_{ON}=600m\Omega$ ($V_{IN}=5V$, $T_j=25^\circ C$, $I_{Dn}=0.2A$)
- Surface mount SSOP-A24 Package
- AEC-Q100 Qualified⁽¹⁾
(1)Grade 1

Product Summary

Digital part Operating voltage	3.0V to 5.5V
Analog part Operating voltage	4.0V to 5.5V
On-state resistance(25°C, Typ)	600mΩ
Over current limit(Typ)	1.80A
Active clamp energy(25°C)	70mJ

Overview

BD8LB600FS-C is an Automotive 8ch Low-Side switch. It has a built-in Over Current Protection circuit, Thermal Shutdown circuit, Open Load Detection circuit, Under Voltage Lock Out circuit, and has a Diagnostic Output(SO) function during abnormal detection.

Application

8ch Low-side switch for driving resistive, inductive, capacitive load

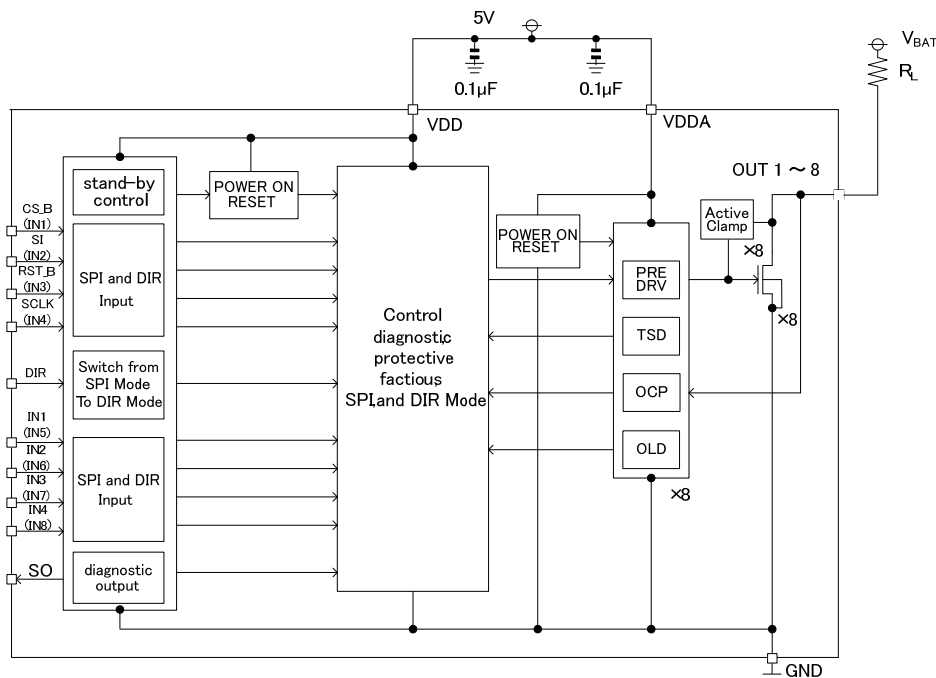
Package

SSOP-A24

10.00mm x 7.80mm x 2.10mm



Basic Application Circuit (Recommendation)



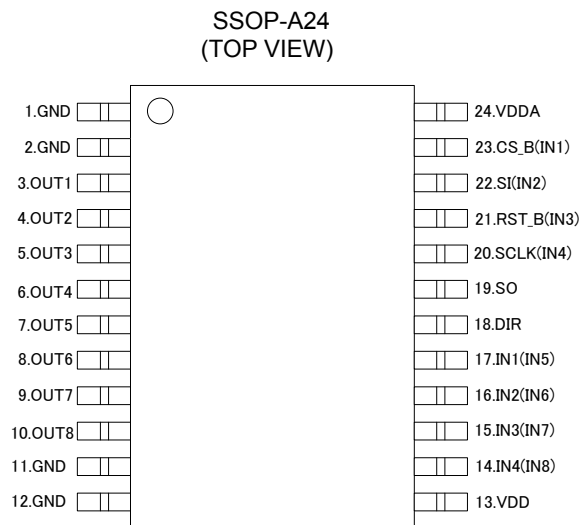
○Product configuration: Silicon monolithic integrated circuit ○The product is not designed for radiation resistance.

Pin Descriptions

Pin	Symbol	I/O ⁽¹⁾		Function
1	GND	-		GND
2	GND	-		GND
3	OUT1	O		Channel 1 output
4	OUT2	O		Channel 2 output
5	OUT3	O		Channel 3 output
6	OUT4	O		Channel 4 output
7	OUT5	O		Channel 5 output
8	OUT6	O		Channel 6 output
9	OUT7	O		Channel 7 output
10	OUT8	O		Channel 8 output
11	GND	-		GND
12	GND	-		GND
13	VDD	-		Digital power supply
14	IN4(IN8)	I	PD	Control input for Channel 4 and 8 (DIR=L) / Control input for Channel 8 (DIR=H)
15	IN3(IN7)	I	PD	Control input for Channel 3 and 7 (DIR=L) / Control input for Channel 7 (DIR=H)
16	IN2(IN6)	I	PD	Control input for Channel 2 and 6 (DIR=L) / Control input for Channel 6 (DIR=H)
17	IN1(IN5)	I	PD	Control input for Channel 1 and 5 (DIR=L) / Control input for Channel 5 (DIR=H)
18	DIR	I	PD	SPI mode, DIR mode change input terminal
19	SO		O	Serial data output terminal
20	SCLK(IN4)	I	PD	Serial clock (DIR=L) / Control input for Channel 4 (DIR=H)
21	RST_B(IN3)	I	PD	Reset terminal (DIR=L) / Control input for Channel 3 (DIR=H)
22	SI(IN2)	I	PD	Serial data input (DIR=L) / Control input for Channel 2 (DIR=H)
23	CS_B(IN1)	I	PU/PD ⁽²⁾	SPI enable input (DIR=L) / Control input for Channel 1 (DIR=H)
24	VDDA	-		Analog power supply

- (1) O : Output terminal, I : Input terminal
 PD : Pull Down terminal, PU : Pull Up terminal
- (2) Pull Up at DIR=Low setting, Pull Down at DIR=High

Pin Configurations



Absolute Minimum Ratings

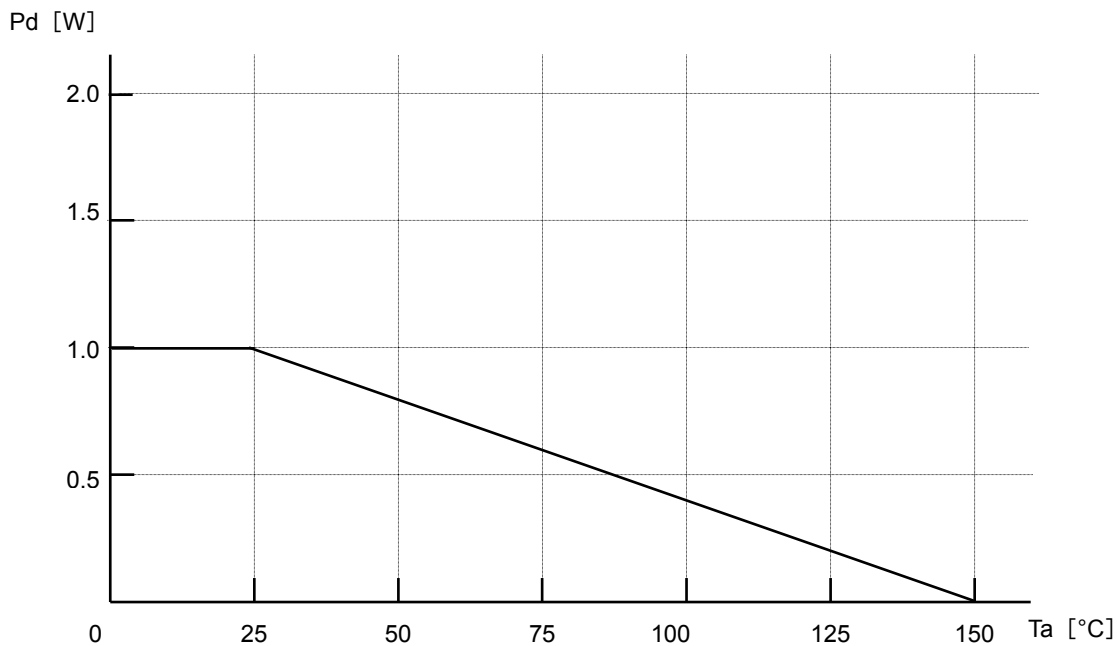
Item	Symbol	Limit values	Unit
DRAIN-SOURCE voltage	V_{DS}	45(Internally limited)	V
Power supply voltage (Logic)	V_{DD}	7 ⁽¹⁾	V
Power supply voltage (Analog)	V_{DDA}	7	V
Diagnostic output voltage	V_{SO}	-0.3 to +7	V
Output current (DC)	I_{OUT}	1.0(Internally limited) ⁽²⁾	A
Output current (Pulse)	I_{OP}	Internally limited ⁽³⁾	A
Input voltage	V_{IN}	-0.3 to +7	V
Power consumption	P_d	1.0(SSOP-A24) ⁽⁴⁾	W
Operating temperature range	T_{opr}	-40 to +150	°C
Storage temperature range	T_{stg}	-55 to +150	°C
Maximum junction temperature	T_{jmax}	150	°C
Active clamp energy (single pulse)	$(T_{j(0)} = 25^{\circ}C)$	70 ⁽⁵⁾	mJ
	$(T_{j(0)} = 150^{\circ}C)$	50 ⁽⁶⁾	mJ

- (1) However, $V_{DD} < V_{DDA} + 0.3V$
- (2) However, exceed neither P_d nor ASO.
- (3) Internally limited by the overcurrent limiting circuit.
- (4) IC mounted on ROHM standard board (70×70×1.6[mm], glass epoxy 1 layer board).
Derate by 8.0mW/°C above 25°C.
- (5) Min Active clamp energy at $T_{j(0)} = 25^{\circ}C$, using single non-repetitive pulse of 0.5A
- (6) Min Active clamp energy at $T_{j(0)} = 150^{\circ}C$, using single non-repetitive pulse of 0.5A. Not 100% tested.

Operating Voltage Ratings

Item	Code	Limit values	Unit
Digital part Operating voltage	V_{DD}	3.0 to 5.5	V
Analog part Operating voltage	V_{DDA}	4.0 to 5.5	V

Heat Dissipation Characteristic



(SSOP-A24) IC mounted on ROHM standard board (70×70×1.6[mm], glass epoxy 1 layer board).
Derate by 8.0mW/°C above 25°C.

Electrical Characteristics (unless otherwise specified, VDDA=5V, VDD=5V, -40°C ≤ Tj ≤ +150°C)

Item	Symbol	Limit values			Unit	Condition
		Min	Typ	Max		
[Power Supply Block]						
VDDA Standby current (All output on standby mode)	I _{DDAS}	-	0	20	μA	VDDA=VDD=5V, CS_B=5V, RST_B=0V
VDD Standby current (All output on standby mode)	I _{DDS}	-	0	20	μA	VDDA=VDD=5V, CS_B=5V, RST_B=0V
VDDA Operating current)	I _{DDA}	-	2	5	mA	VDDA=VDD=5V
VDD Operating current)	I _{DD}	-	0.5	1	mA	VDDA=VDD=5V
VDDA power on reset Threshold Voltage	V _{PORA}	-	-	4.0	V	
VDD power on reset Threshold Voltage	V _{POR}	-	-	2.7	V	
[Input PIN]						
L level input voltage	V _{INL}	0	-	VDD×0.2	V	
H level input voltage	V _{INH}	VDD×0.7	-	VDD	V	
Input Hysteresis	V _{HYS}	0.1	0.3	0.5	V	
L level input current 1 (RST_B, DIR, IN1 to IN4, SCLK, SI)	I _{INL1}	-10	0	10	μA	RST_B=DIR=IN1 to IN4=SCLK =SI=0V
L level input current 2(CS_B)	I _{INL2}	-100	-50	-25	μA	CS_B(DIR=L)=0V
H level input current 1 (RST_B, DIR, IN1 to IN4, SCLK, SI)	I _{INH1}	25	50	100	μA	RST_B=DIR=IN1 to IN4=SCLK =SI=5V
H level input current 2(CS_B)	I _{INH2}	-10	0	10	μA	CS_B(DIR=L)=5V
[Power MOS Output]						
Output ON resistance	R _{DS(ON)}	-	0.6	0.8	Ω	VDD=VDDA=5V, I _{DS} =0.2A, Tj=25°C
		-	1.1	1.4	Ω	VDD=VDDA=5V, I _{DS} =0.2A, Tj=150°C
Output sink current	I _{L(OFF)}	-	10	20	μA	V _{DS} =30V, Tj=25°C
		-	15	40	μA	V _{DS} =30V, Tj=150°C
Output leak current (Open load detected)	I _{OL}	25	50	100	μA	V _{DS} =40V
Switching time	t _{ON}	-	20	50	μs	VDD=VDDA=5V, CS_B=0V/5V, R _L =60Ω, V _B =12V
	t _{OFF}	-	20	50	μs	VDD=VDDA=5V, CS_B=0V/5V, R _L =60Ω, V _B =12V
Slew rate on	dV/dt _{ON}	0.3	1	3	V/μs	VDD=VDDA=5V, CS_B=0V/5V, R _L =60Ω, V _B =12V
Slew rate off	-dV/dt _{OFF}	0.3	1	3	V/μs	VDD=VDDA=5V, CS_B=0V/5V, R _L =60Ω, V _B =12V
PWM Output range	f _{PWM}	-	-	1.2	kHz	VDD=VDDA=5V, I _{Nn} =0V/5V, R _L =60Ω, V _B =12V
Output clamp voltage	V _{CL}	45	50	55	V	I _{DS} =1mA(at Output turn off)
Minimum Output Voltage (Load short-circuited)	V _{DS(S)}	31	-	-	V	I _{Nn} ⁽¹⁾ =5V, R _L =0Ω

(1) n means ch number

Electrical Characteristics (unless otherwise specified, VDDA=5V, VDD=5V, -40°C ≤ Tj ≤ +150°C)

Item	Symbol	Limit values			Unit	Condition
		Min	Typ	Max		
[Serial Output]						
L level output voltage	V _{SOL}	-	0.3	0.6	V	I _{SO} =1mA
H level output voltage	V _{SOH}	VDD-0.6	VDD-0.3	-	V	I _{SO} =-1mA
Serial out output leak current	I _{SO(OFF)}	-5	0	5	μA	
[Protect circuit]						
Over current detection current	I _{OCP(ON)}	1.00	1.80	3.00	A	
Over current release current	I _{OCP(OFF)}	0.70 ⁽¹⁾	1.26 ⁽¹⁾	2.10 ⁽¹⁾	A	
Over current detection time	t _{OCP}	50	250	600	μs	
Open Load release voltage	V _{OLD(ON)}	0.70	1.50	2.70	V	I _{Nn} ⁽²⁾ =0V
Open load detection threshold voltage	V _{OLD(OFF)}	1.00	1.75	3.00	V	I _{Nn} ⁽²⁾ =0V
Open load detection time	t _{OLD}	50	300	600	μs	I _{Nn} ⁽²⁾ =0V

(1) Not 100% tested
 (2) n means ch number

Definition

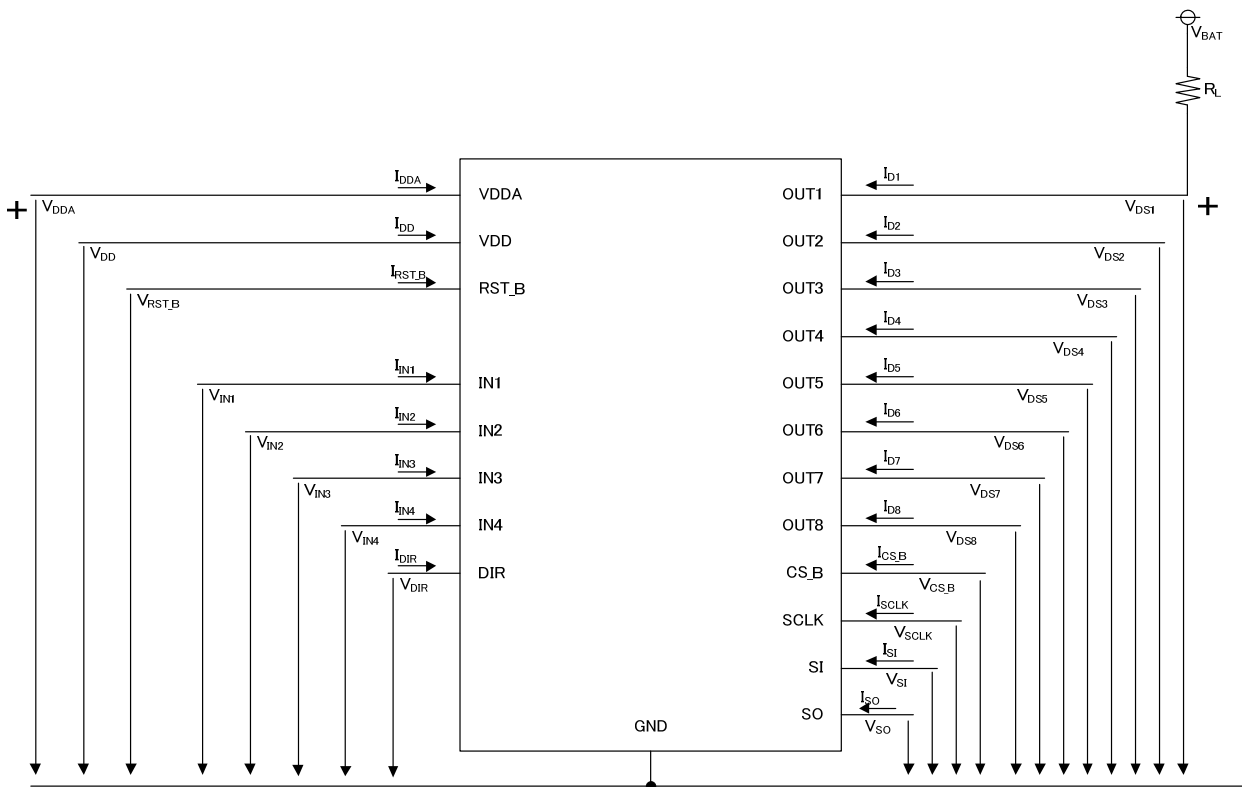


Figure 1. Definition

Measurement Circuit

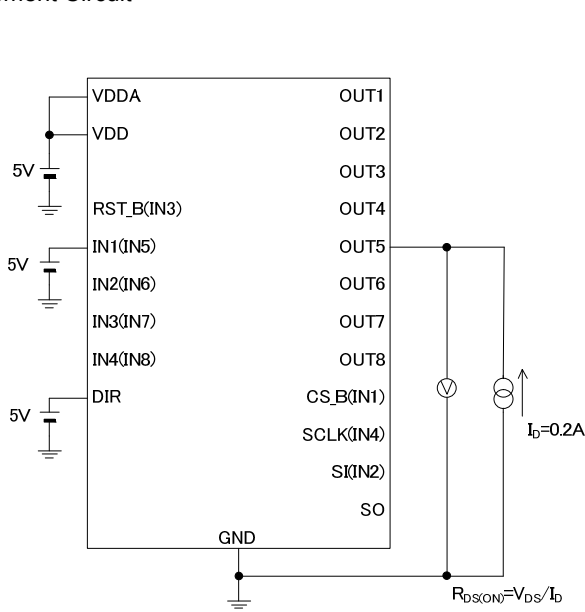


Figure 2. Output ON Resistance Measuring Circuit Diagram

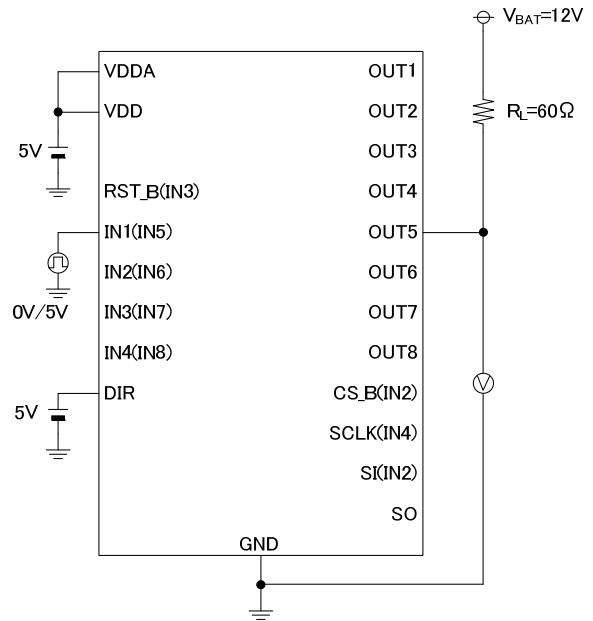


Figure 3. Switching Time Measuring Circuit Diagram

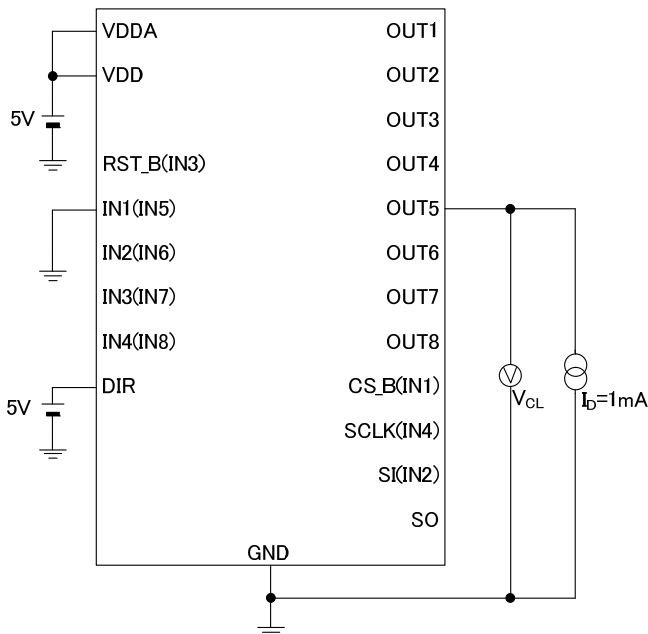


Figure 4. Output Clamp Voltage Measuring Circuit Diagram

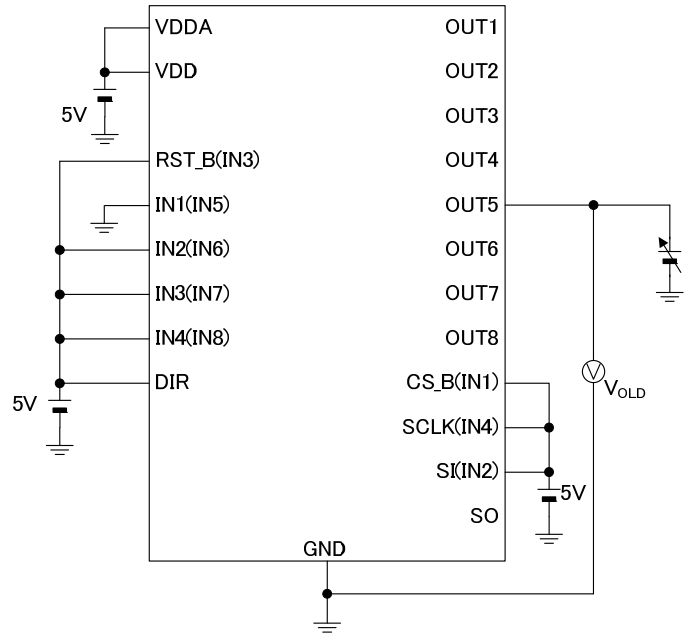


Figure 5. Open Detection Measuring Circuit Diagram

DIR(Direct)mode Diagnostic Output Truth Table

V _{IN}	T _j	OUTPUT		mode	V _{SO}	Output state
		V _{DS}	I _D			
H	T _j < 175°C(Typ)	-	I _D ≤ 1.8A(Typ)	Normal	L	ON
			I _D > 1.8A(Typ)	Over current detection	H	OFF
	T _j ≥ 175°C(Typ)	-	-	Thermal shut down	H	OFF
L	-	H (3.0V or more)	-	Normal	L	OFF
		L (1.5V(Typ) or less)	-	Open load detection	H	OFF

Characteristic Data (Reference Data) ($V_{DD}=5V$, $V_{DDA}=5V$, $I_N=5V$, $T_j=25^\circ C$ unless otherwise is specified)

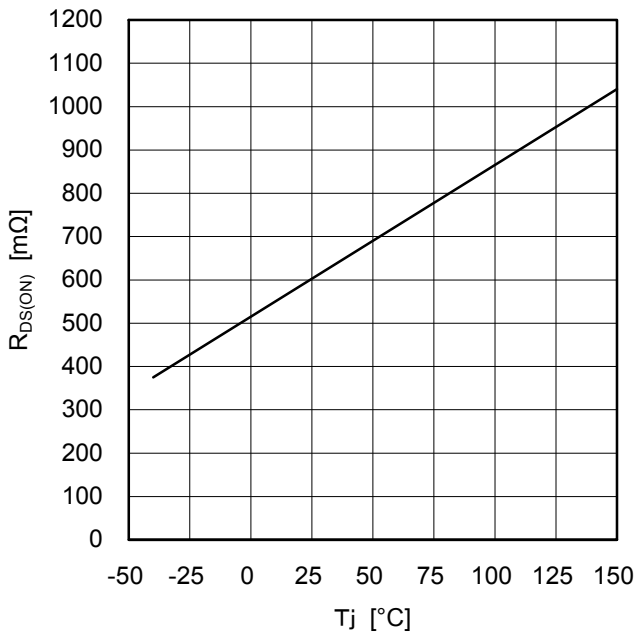


Figure 6. Output ON Resistance Characteristic [Temperature Characteristic]

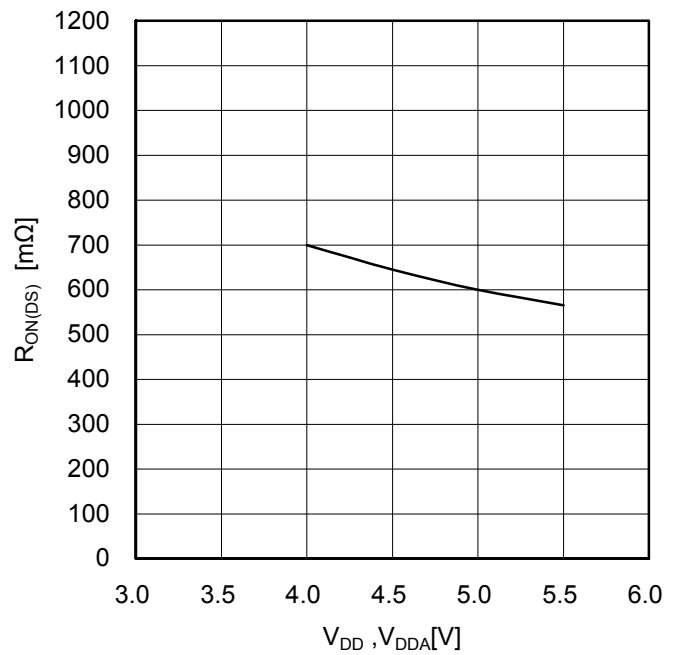


Figure 7. Output ON Resistance Characteristic [Source Voltage Characteristic]

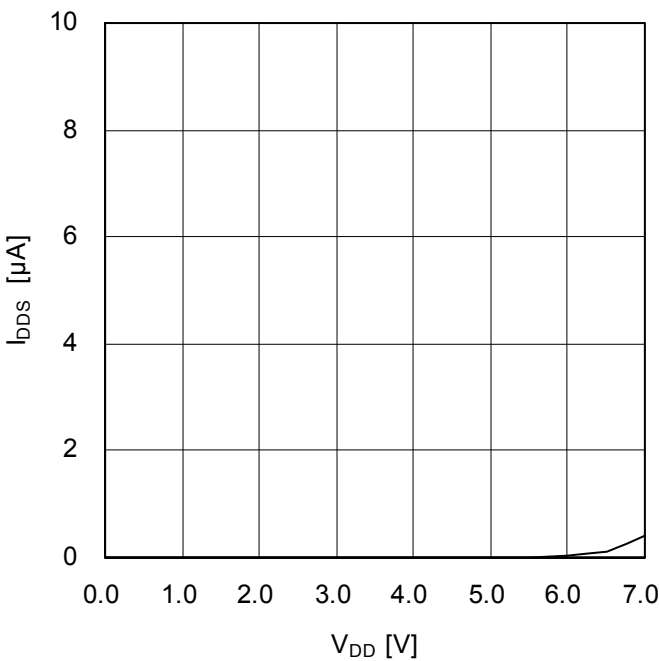


Figure 8. Standby Current Characteristic (VDD)

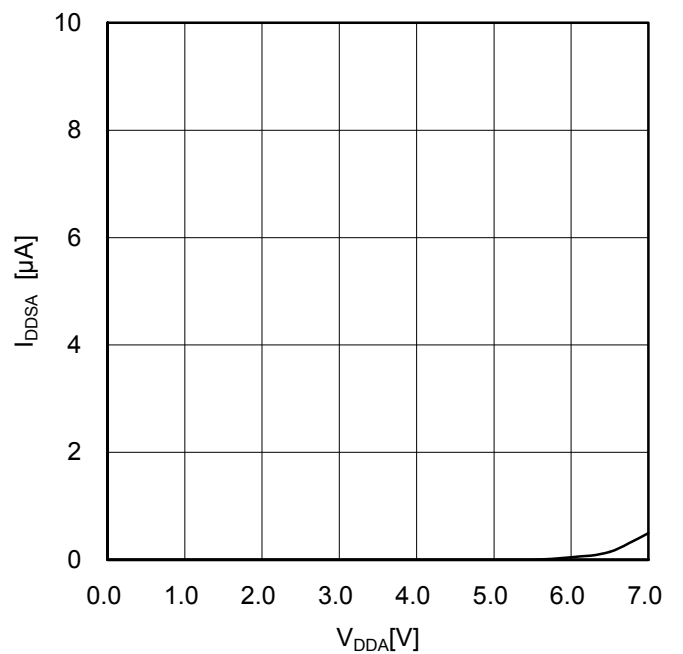


Figure 9. Standby Current Characteristic (VDDA)

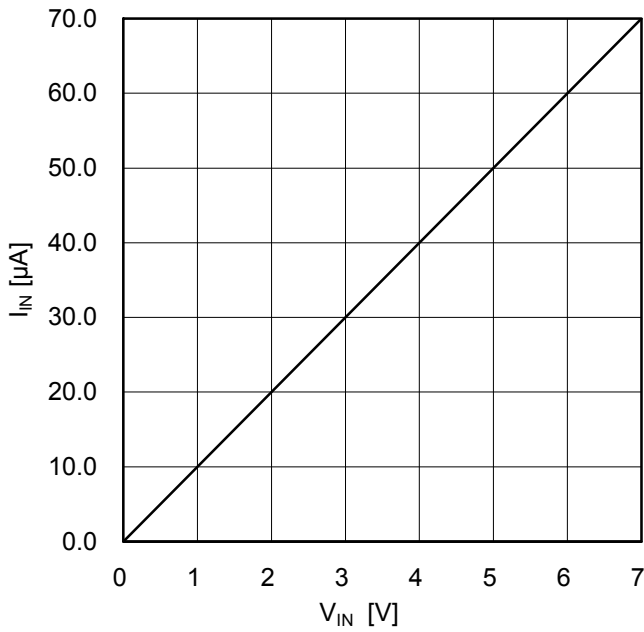


Figure 10. Input current Characteristic (IN1 to 4, DIR, SCLK, SI, RST_B)

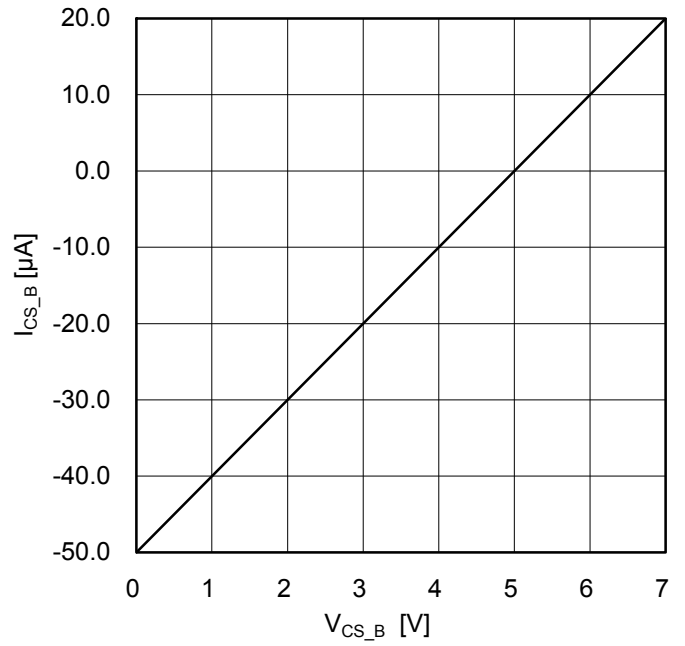


Figure 11. Input current Characteristic (CS_B)

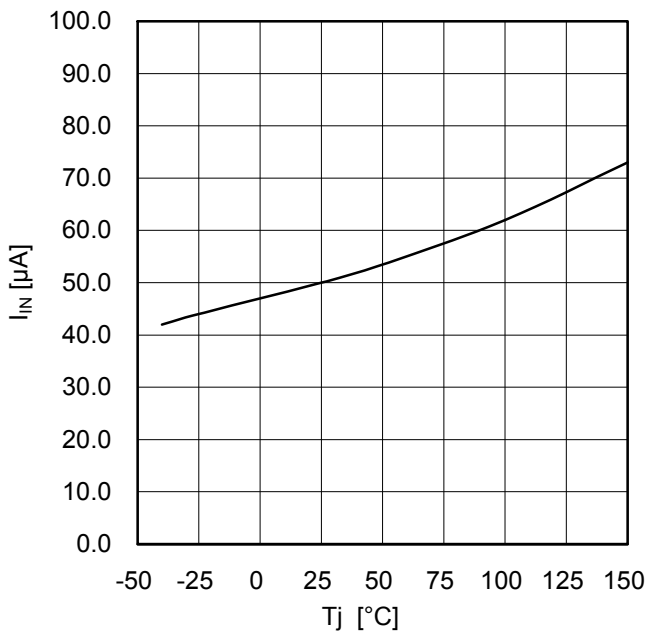


Figure 12. Input current Characteristic [Temperature Characteristic] (IN1 to 4, DIR, SCLK, SI, RST_B=5V, CS_B=0V)

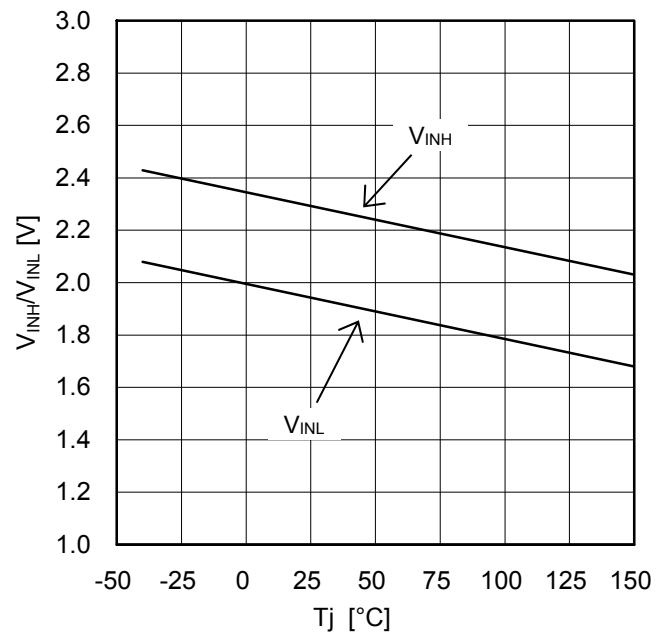


Figure 13. Input Voltage Threshold Characteristic [Temperature Characteristic]

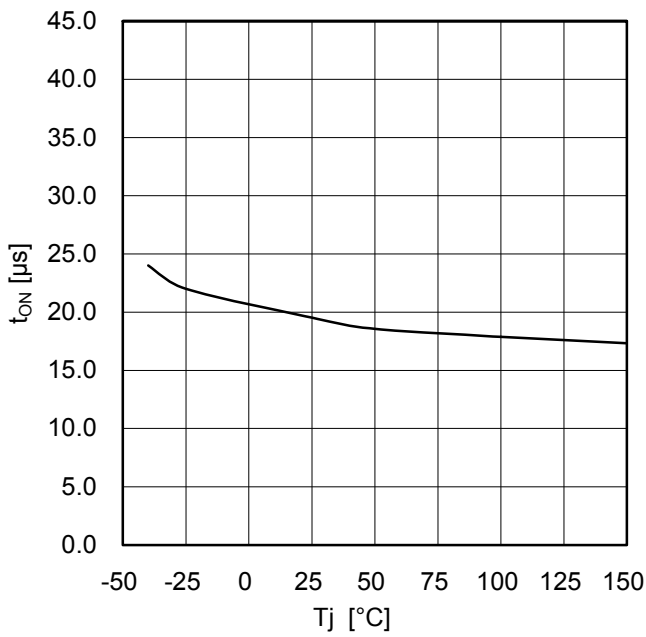


Figure 14. Switching Time (t_{ON}) [Temperature Characteristic]

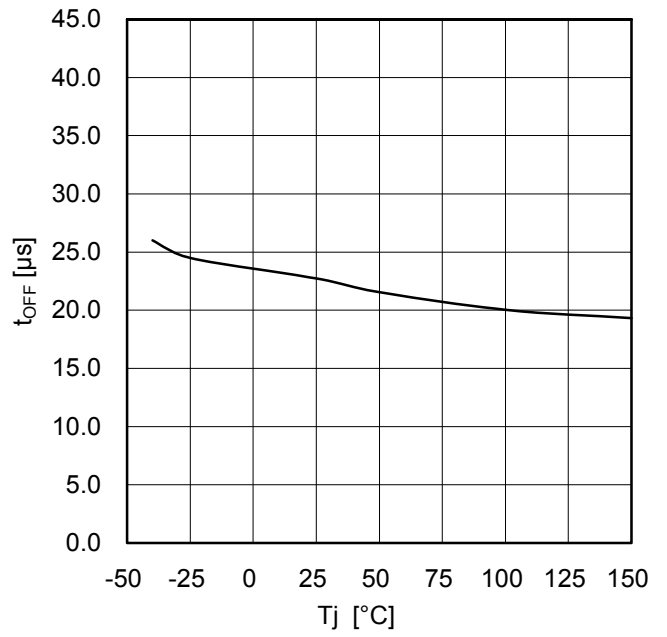


Figure 15. Switching Time (t_{OFF}) [Temperature Characteristic]

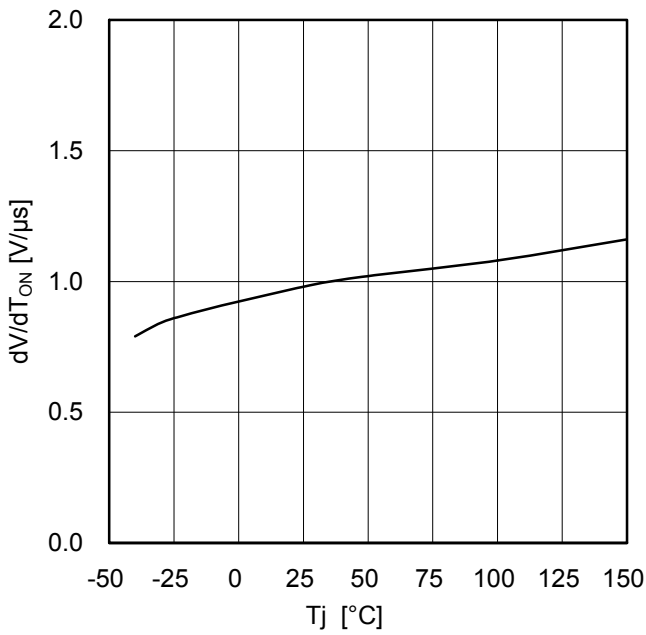


Figure 16. Slew Rate (at ON) [Temperature Characteristic]

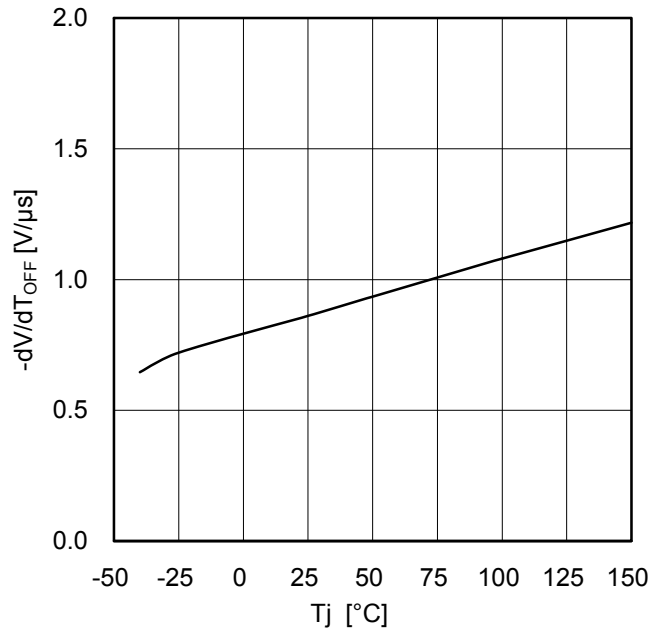


Figure 17. Slew Rate (at OFF) [Temperature Characteristic]

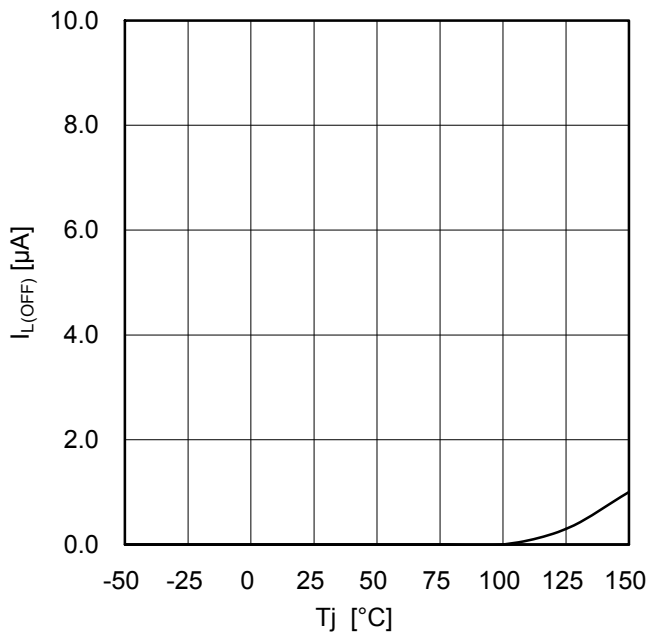


Figure 18. Output Leak Current [Temperature Characteristic](VDS=30V)

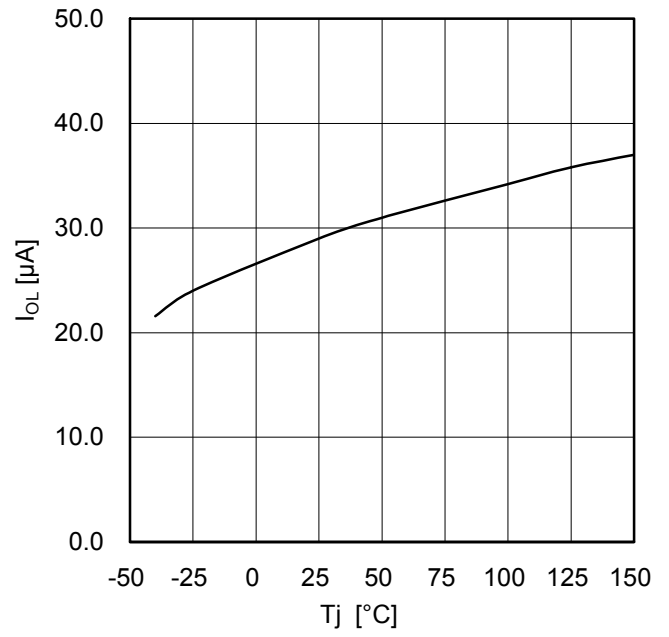


Figure 19. Output Leak Current (Open detect) [Temperature Characteristic](VDS=40V)

Switching Time Measurement

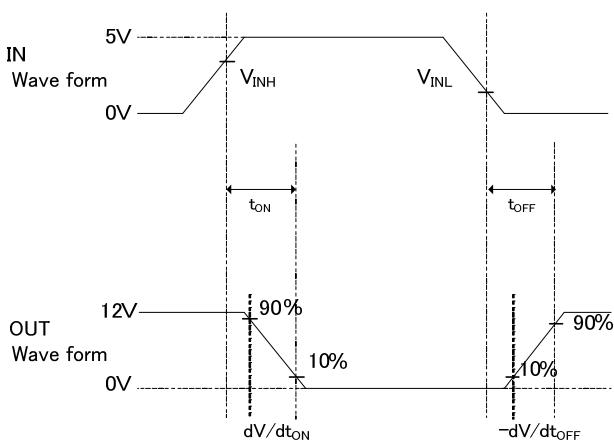


Figure 20. Switching Time

Timing Chart with Inductive Load

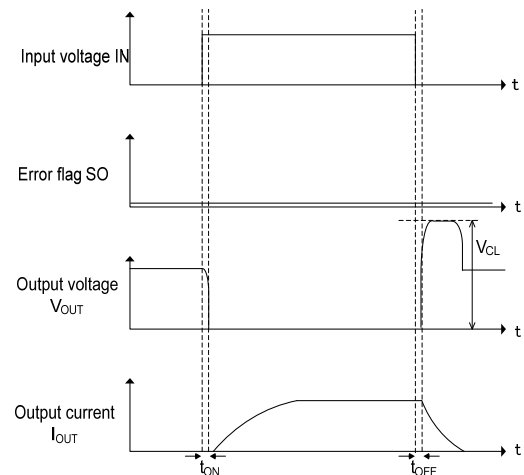


Figure 21. Timing Chart with inductive Load

I/O Equivalent Circuits

Pin	Symbol	I/O Equivalent Circuits
1,2, 11,12	GND	
3 to 10	OUT1 to OUT8	
13	VDD	
14 to 17 18 20 to 22	IN4(IN8), IN3(IN7), IN2(IN6), IN1(IN5), DIR, SCLK(IN4), RST_B(IN3), SI(IN2)	
19	SO	
23	CS_B	
24	VDDA	

SPI mode(DIR=L)

When CS_B=H,

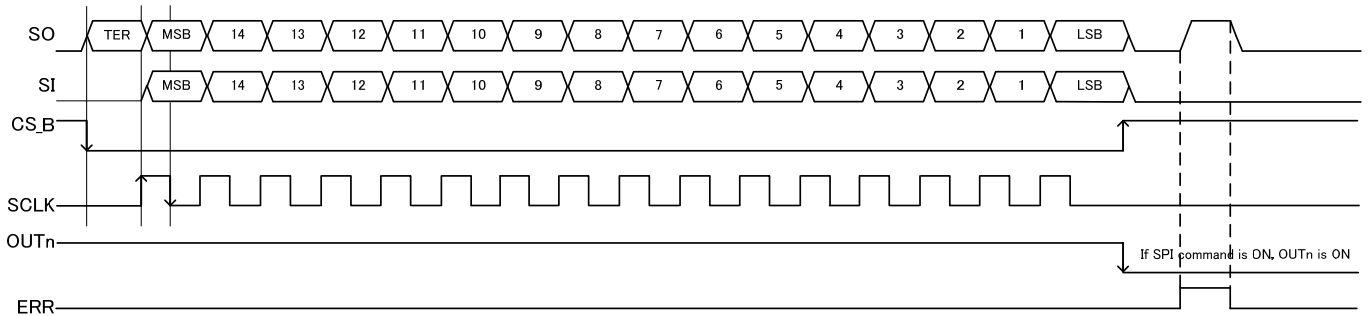
OR signal (ERR) of SI and abnormal signal (TER, TSD, OCP, OLD) is output to SO terminal.

When CS_B=L,

Internal state (TSD, OCP, OLD) is latched at falling edge of CS_B, and output to SO at rising edge of SCLK.

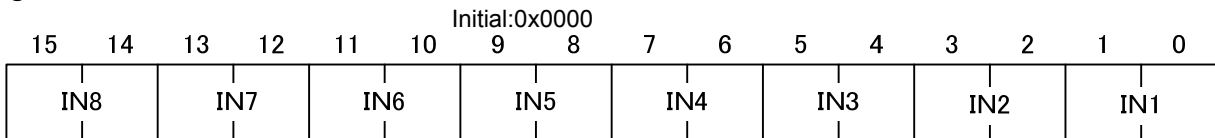
SI is taken in register at falling edge of SCLK.

Output corresponding to each register input is controlled at rising edge of CS_B.



Definitions of SI and SO signals are shown below.

SI signals



Bits	INn	States of output and protective circuits			
		Output	OCP	TSD	OLD
15:14, 13:12, 11:10, 9:8, 7:6, 5:4, 3:2, 1:0	00	OFF	disable	disable	disable
	01	ON/OFF ⁽¹⁾	enable/disable	enable/disable	disable/enable
	10	ON	enable	enable	disable
	11	OFF	disable	disable	enable

(1) When INn=01, output is controlled by IN terminal.

Output controlled by each input is shown below.

Input	Controlled output
IN1(IN5)	OUT1
IN2(IN6)	OUT2
IN3(IN7)	OUT3
IN4(IN8)	OUT4
IN1(IN5)	OUT5
IN2(IN6)	OUT6
IN3(IN7)	OUT7
IN4(IN8)	OUT8

SO signals

When CS_B=H,

OR signal (ERR) of abnormal signal (SI, TER, TSD, OCP, OLD) is output to SO terminal.

When CS_B=L,

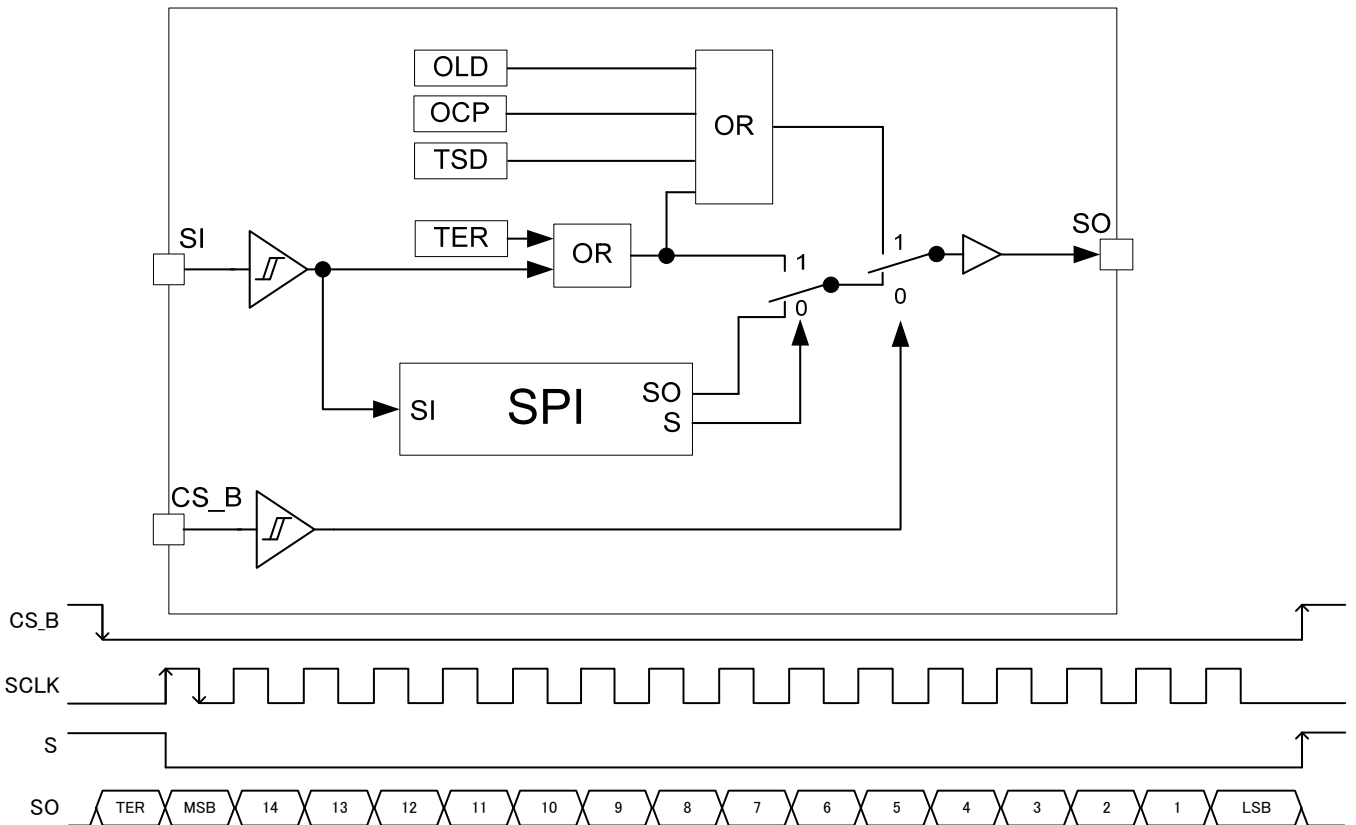
Explanation of each Bit is shown below.

16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
TER	OL8	D8	OL7	D7	OL6	D6	OL5	D5	OL4	D4	OL3	D3	OL2	D2	OL1	D1
OUT8		OUT7		OUT6		OUT5		OUT4		OUT3		OUT2		OUT1		

Bits	Data	STATE
16 ⁽¹⁾	0	Correspondence just after reset and normal operation
	1	Correspondence error of last time
15,13,11 9,7,5 3,1	0	Normal operation
	1	Load open
14,12 10,8,6 4,2,0	0	Normal operation
	1	OCP or TSD

(1) TER bit outputs logical sums of TER signal and input signal of this device with SI signal in the interval from fall of CS_B to rise of SCLK as shown below.

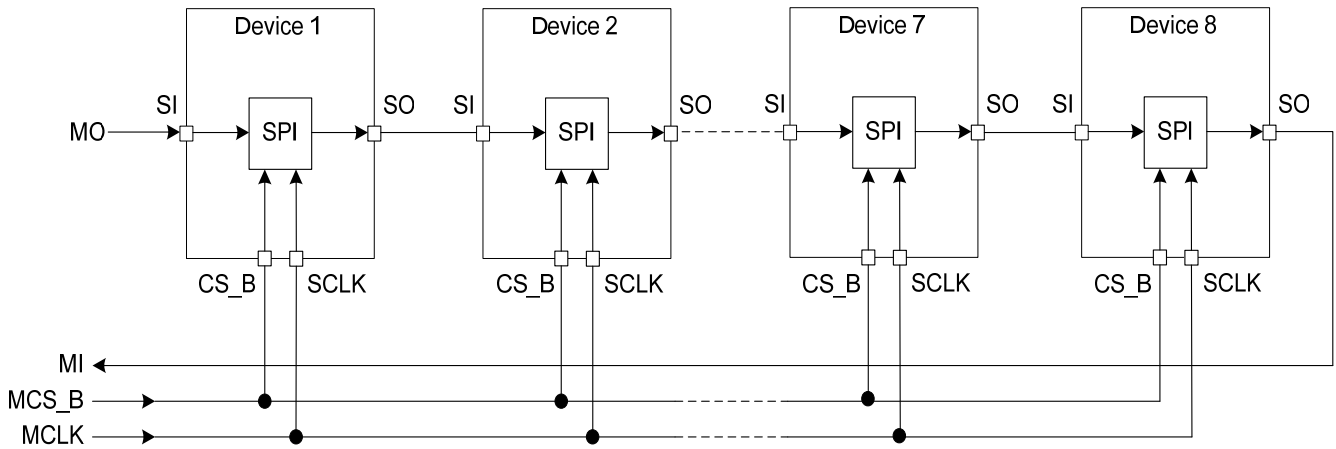
Block diagram and timing chart are shown below.



In order to select whether TER signal is output or SPI data output (OLn, Dn) signal is output, “S” signal is generated within IC and output is switched.

Daisy Chain

Plurality of devices can be connected as shown in the diagram below.
 CS_B signal and SCLK signal connects common signal.
 SI/SO line can connect SO of Device 1 to SI of Device 2 as shown in the diagram below.



Timing chart when 8 devices are connected is shown below.

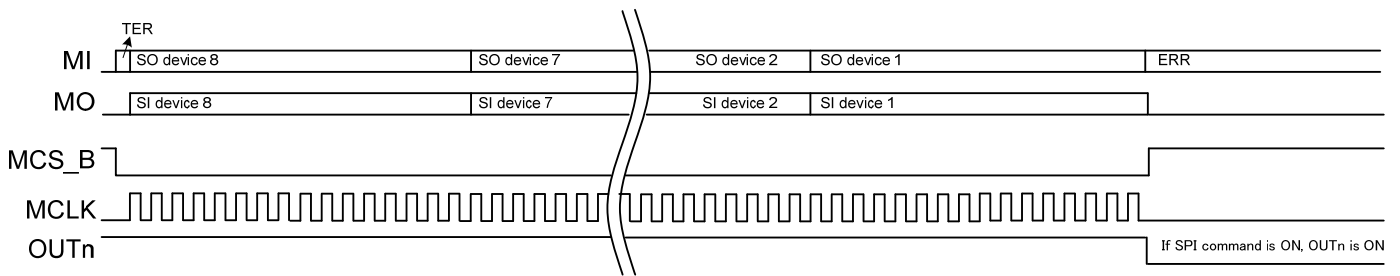


Figure 22. Timing chart when 8 devices are connected

SPI RST_B releasing sequence

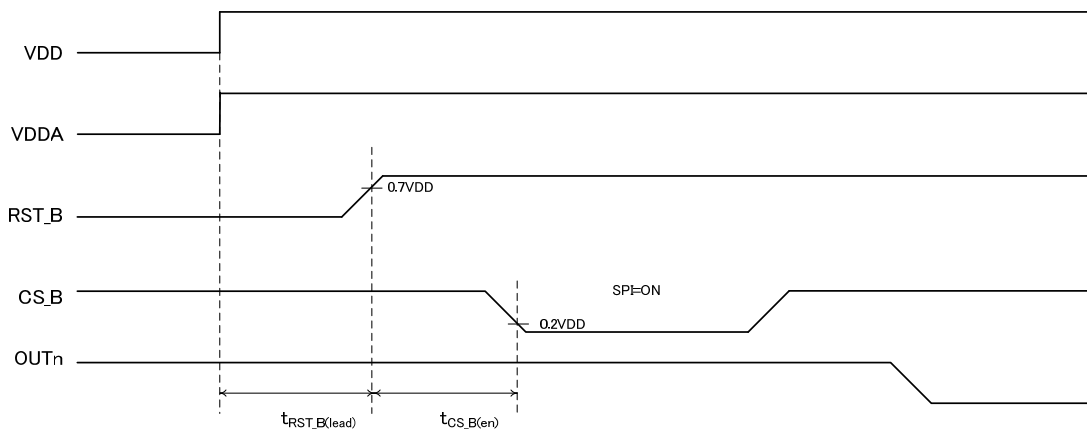


Figure 23. RST_B Releasing Sequence

Item	Signal	Minimum	Standard	Minimum	Unit
RST_B lead time ^{(1) (2)}	t _{RST_B (lead)}	1	-	-	ms
CS_B enable time ⁽¹⁾	t _{CS_B (en)}	10	-	-	μs

(1) Not 100% tested
 (2) RST_B L time and H time must be over 10μs

SPI timing chart

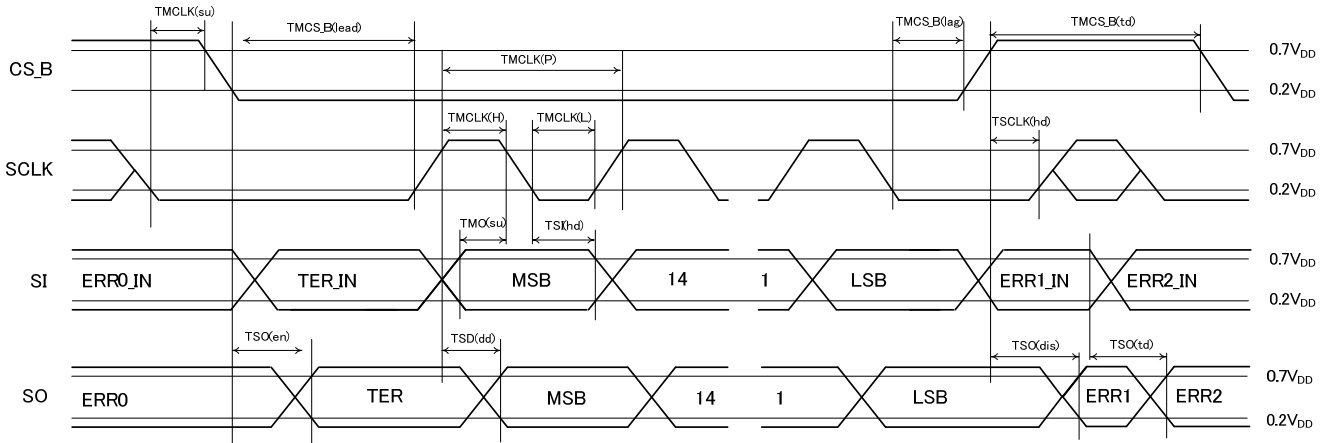


Figure 24. SPI Timing Chart

Item	Signal	Minimum	Standard	Minimum	Unit
SCLK frequency	fSCLK	0	—	5	MHz
SCLK cycle length	TSCLK(P)	200	—	—	ns
SCLK high time	TSCLK(H)	50	—	—	ns
SCLK lo time	TSCLK(L)	50	—	—	ns
SCLK setup time	TSCLK(su)	50	—	—	ns
SCLK hold time	TSCLK(hd)	50	—	—	ns
CS_B lead time	TCS_B(lead)	250	—	—	ns
CS_B lag time	TCS_B(lag)	250	—	—	ns
Transfer delay time	TCS_B(td)	250	—	—	ns
Data setup time	TSI(su)	20	—	—	ns
Data hold time	TSI(h)	20	—	—	ns
SPI Output enable time ⁽¹⁾	TSO(en)	—	—	200	ns
SPI Output disable time ⁽¹⁾	TSO(dis)	—	—	250	ns
SPI Output Data delay time ⁽¹⁾	TSO(dd)	—	—	100	ns
ERR Output Through delay time ⁽¹⁾	TSO(td)	—	—	200	ns

(1) Not 100% tested. When SO terminal capacity=10pF.

DIR (direct) mode

Transition to direct mode is brought about by switching DIR terminal to High.
 Output controlled for each input is shown below.
 Further, SPI input and RST_B input are not accepted during direct mode.

Input	Controlled Output
CS_B(IN1)	OUT1
SI(IN2)	OUT2
RST_B(IN3)	OUT3
SCLK(IN4)	OUT4
IN1(IN5)	OUT5
IN2(IN6)	OUT6
IN3(IN7)	OUT7
IN4(IN8)	OUT8

DIR (direct) mode timing chart (1)

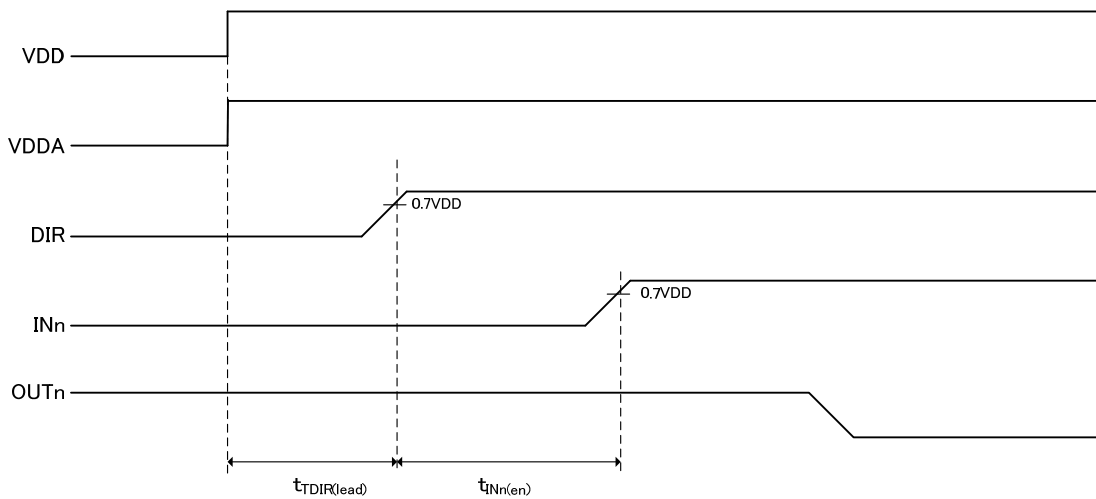


Figure 25. DIR Mode Timing Chart (1)

Item	Signal	Minimum	Standard	Minimum	Unit
DIR lead time ⁽¹⁾	t _{DIR(lead)}	1	-	-	ms
INn enable time ⁽¹⁾	t _{INn(en)}	10	-	-	μs

(1) Not 100% tested.

DIR (direct) mode timing chart (2)

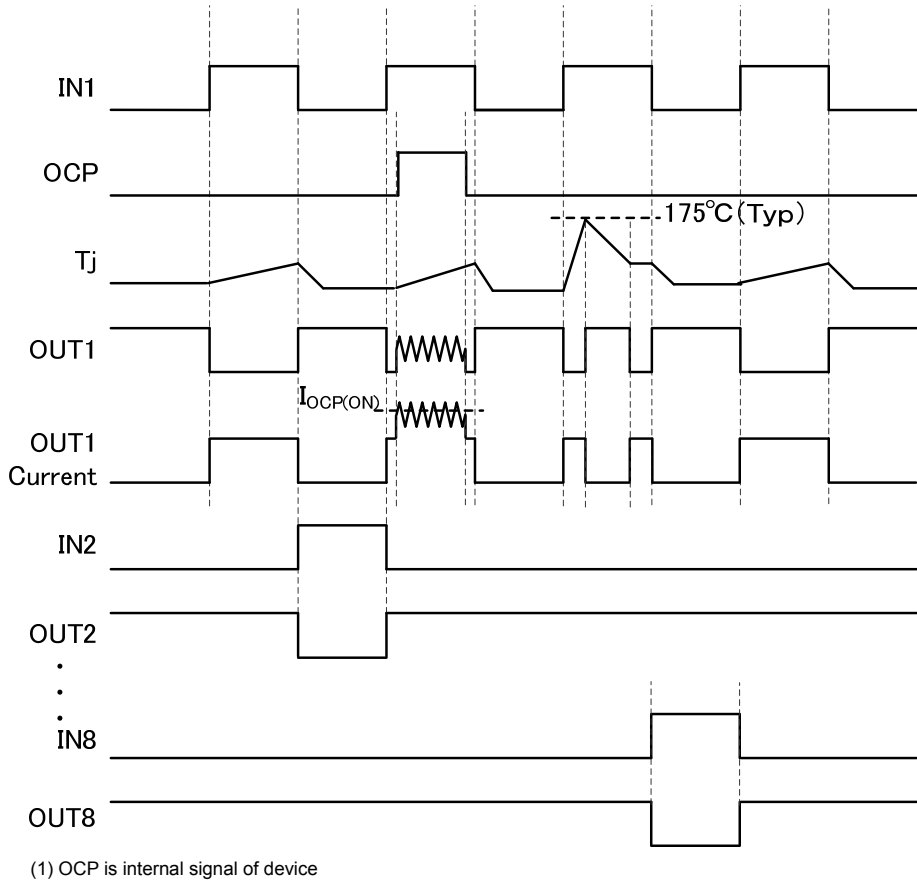


Figure 26. DIR Mode Timing Chart (2)

Direct mode operation current (I_{DDA} + I_{DD}) state transition

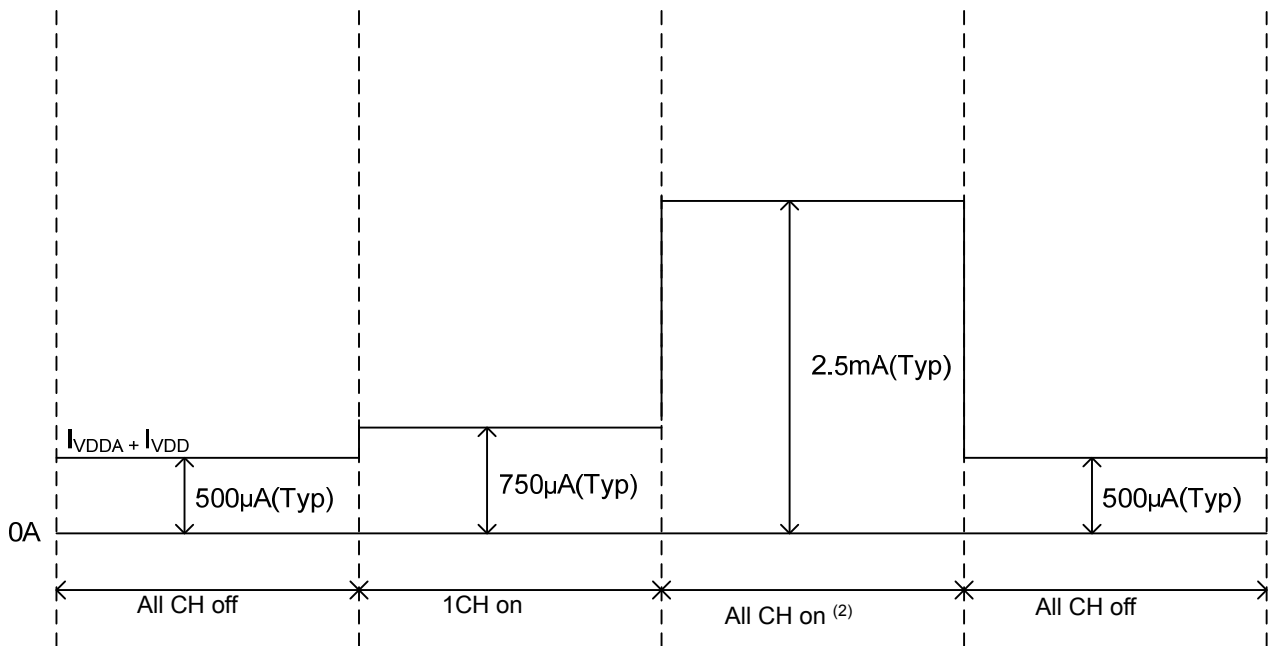


Figure 27. Operation Current State Transition Diagram

(2) Sum of P.4 VDDA operation current (when all outputs are on) and VDD operation current (when all outputs are on).

Power source ON/OFF sequence

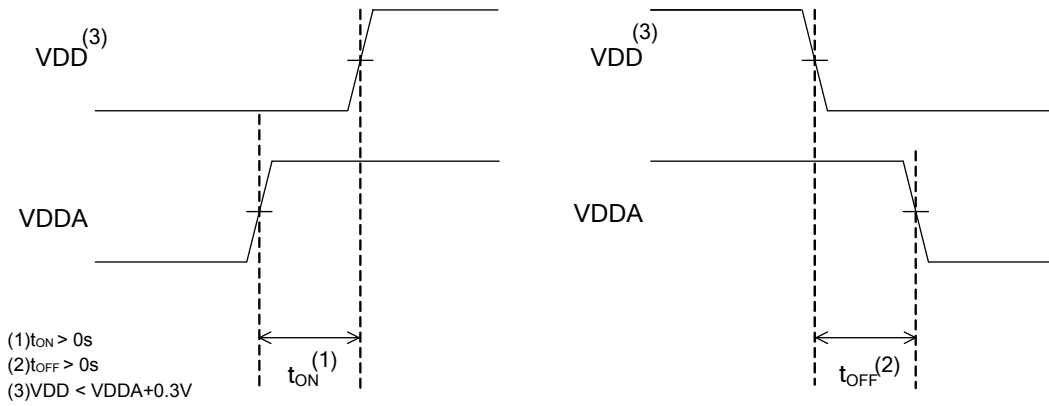


Figure 28. Power Source ON/OFF Sequence

Detection functions

① Overcurrent protection

When current of no less than 1.8 A (Typ) is flown in output transistor of from OUT1 to OUT8 in 250 μs (Typ), error flag is output.

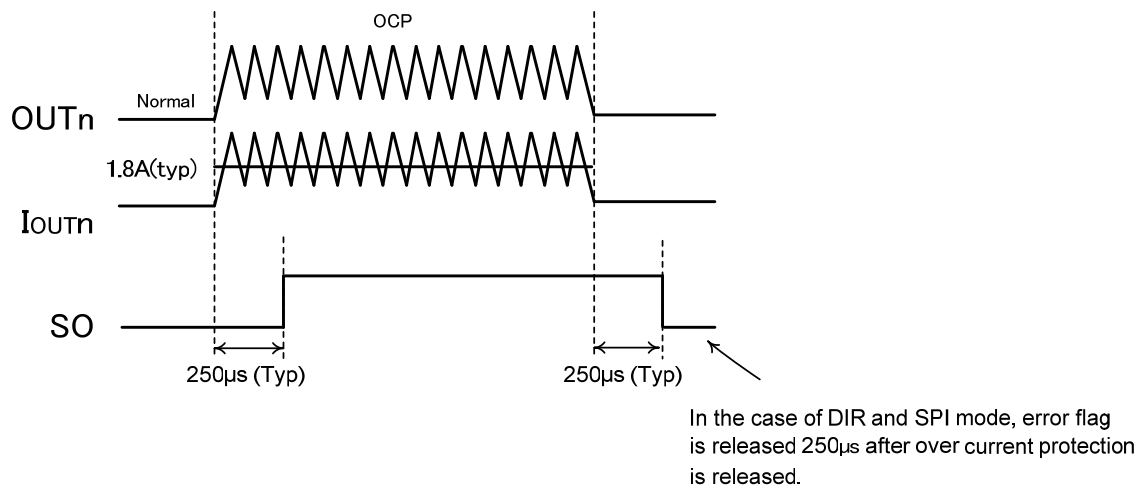


Figure 29. Overcurrent Protection Timing Chart

② Overheat protection

Junction temperature of from OUT1 to OUT8 reaches 175°C (Typ) or above, output is turned off. It is automatically turned on at 150°C (Typ) or below

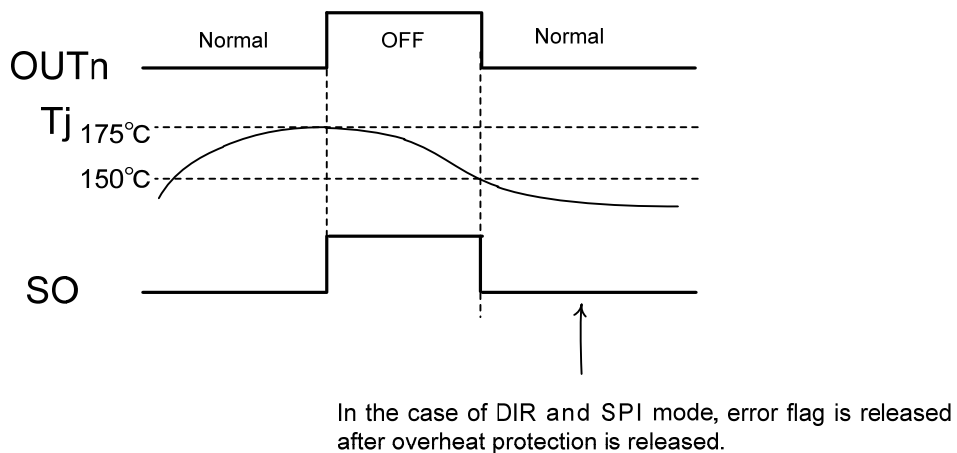
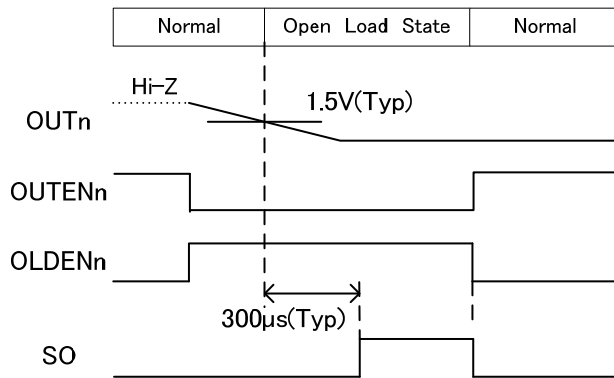


Figure 30. Overheat Protection Timing Chart

③ Open detection

In case of enable at Open detection function⁽¹⁾, when output current of from OUT1 to OUT8 falls below 1.5 V (Typ), open detection is detected and error flag is output.

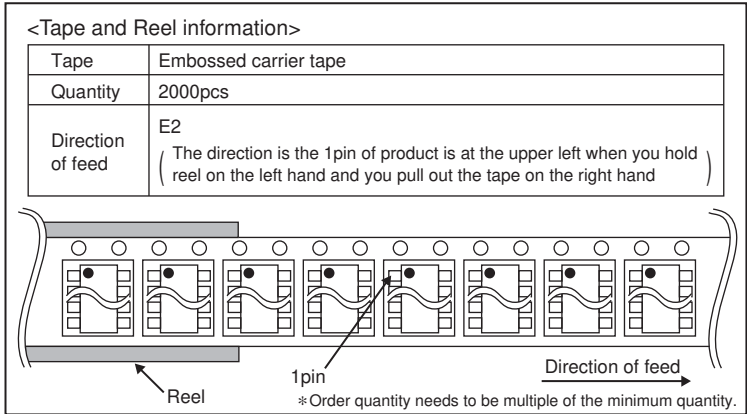
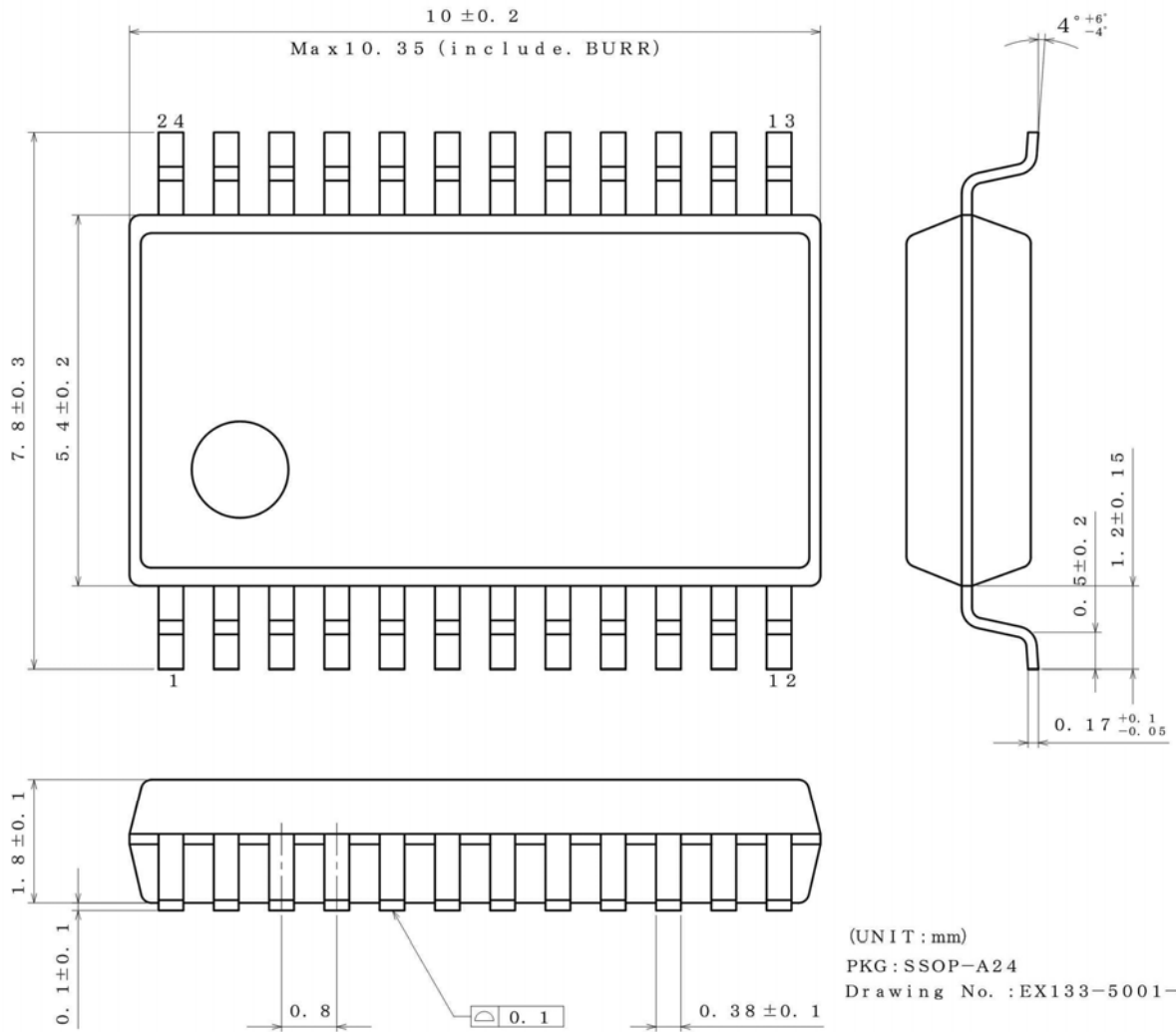


(1) As for the DIR mode, OLDENn=H(open detection function becomes effective) in OUTENn=L.
 As for the SPI mode, Please refer to "SI Signals" (Page 13/24).
 "n" shows the channel number.

Figure 31. Open Detection Protection Timing Chart

Physical Dimension, Tape and Reel Information

Package Name	SSOP-A24
--------------	----------



Operational Notes

- 1) Absolute Minimum Ratings
Operating the IC over the absolute Minimum ratings may damage the IC. In addition, it is impossible to predict all destructive situations such as short-circuit modes or open circuit modes. Therefore, it is important to consider circuit protection measures, like adding a fuse, in case the IC is expected to be operated in a special mode exceeding the absolute Minimum ratings.
- 2) Reverse connection of power supply
Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply terminals.
- 3) Power supply lines
Design the PCB layout pattern to provide low impedance ground and supply lines. Separate the ground and supply lines of the digital and analog blocks to prevent noise in the ground and supply lines of the digital block from affecting the analog block. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.
- 4) Source (GND) Voltage
The voltage of the Source (GND) pin must be the lowest voltage of all pins of the IC at all operating conditions. Ensure that no pins are at a voltage below the ground pin at any time, even during transient condition.
- 5) Thermal consideration
Use a thermal design that allows for a sufficient margin by taking into account the permissible power dissipation (Pd) in actual operating conditions. Consider Pc that does not exceed Pd in actual operating conditions ($P_c \geq P_d$).

Package Power dissipation : $P_d (W) = (T_{jmax} - T_a) / \theta_{ja}$

Power dissipation : $P_c (W) = (V_{cc} - V_o) \times I_o + V_{cc} \times I_b$

T_{jmax} : Minimum junction temperature = 150°C, T_a : Peripheral temperature [°C],

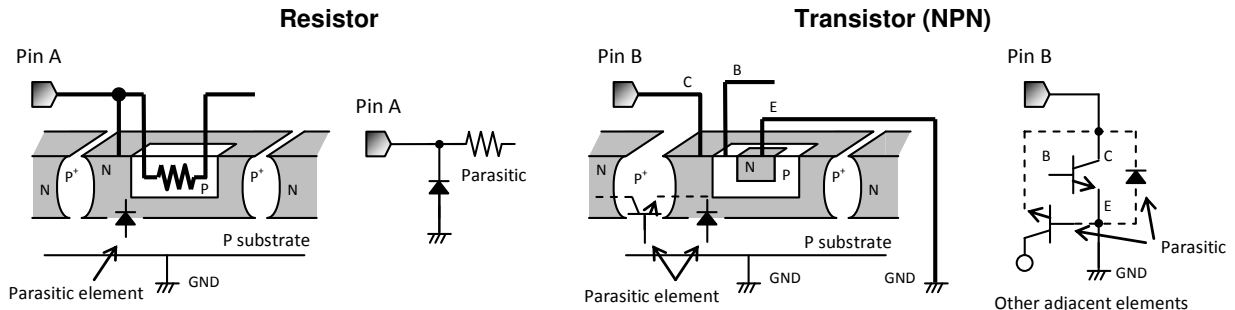
θ_{ja} : Thermal resistance of package-ambience [°C /W], P_d : Package Power dissipation [W],

P_c : Power dissipation [W], V_{cc} : Input Voltage, V_o : Output Voltage, I_o : Load, I_b : Bias Current

- 6) Short between pins and mounting errors
Be careful when mounting the IC on printed circuit boards. The IC may be damaged if it is mounted in a wrong orientation or if pins are shorted together. Short circuit may be caused by conductive particles caught between the pins.
- 7) Operation Under Strong Electromagnetic Field
Operating the IC in the presence of a strong electromagnetic field may cause the IC to malfunction.
- 8) Thermal shutdown circuit (TSD)
The IC incorporates a built-in thermal shutdown circuit, which is designed to turn off the IC when the internal temperature of the IC reaches 175°C (25°C hysteresis). It is not designed to protect the IC from damage or guarantee its operation. Do not continue to operate the IC after this function is activated. Do not use the IC in conditions where this function will always be activated.
- 9) Over voltage protection (active clamp)
There is a built-in over voltage protection circuit (active clamp) to absorb the induced current when inductive load is off (Power MOS = off). During active clamp and when $I_N = 0V$, TSD will not function so keep IC temperature below 150°C.
- 10) Over current protection circuit (OCP)
The IC incorporates an over-current protection circuit that operates in accordance with the rated output capacity. This circuit protects the IC from damage when the load becomes shorted. It is also designed to limit the output current (without latching) in the event of more than 1.5A (Typ) flow, such as from a large capacitor or other component connected to the output pin. This protection circuit is effective in preventing damage to the IC in cases of sudden and unexpected current surges. The IC should not be used in applications where the over current protection circuit will be activated continuously.
- 11) Testing on application boards
When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.
- 12) Regarding input pins of the IC
This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When $GND > Pin A$ and $GND > Pin B$, the P-N junction operates as a parasitic diode.
 When $GND > Pin B$, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.



Example of monolithic IC structure

- 13) **GND wiring pattern**
 When using both small-signal and large-current GND traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the GND traces of external components do not cause variations on the GND voltage. The power supply and ground lines must be as short and thick as possible to reduce line impedance.
- 14) **Back electromotive force (BEMF)**
 There is a possibility that the BEMF is changed by using the operating condition, environment and the individual characteristics of motor. Please make sure there is no problem when operating the IC even though the BEMF is changed.
- 15) **Rush Current**
 When power is supplied to the IC, inrush current may flow instantaneously. It is possible that the charge current from the parasitic capacitance of the internal logic may be unstable. Therefore, give a special consideration with the power coupling capacitance, power wiring, width of GND wiring, and routing of connections.

Revision History

Date	Revision	Changes
06.Sep.2013	002	New Release
03.Apr.2015	003	<p>P1 Add "AEC-Q100 qualified" to Features</p> <p>P3 active clamp energy condition added</p> <p>P4 Limit(Typ) of VDDA Operating current changed</p> <p>P4 Limit values of L level input current 2(CS_B) changed</p> <p>P5 Condition of "Open Load release voltage", "Open load detection threshold voltage" and "Open load detection time" added</p> <p>P6 Modify Figure 5.</p> <p>P7 Modify DIR(Direct)mode Diagnostic Output Truth Table</p> <p>P9 Characteristic Data of L level input current 2(CS_B) changed</p> <p>P11 Timing Chart with Inductive Load changed</p> <p>P12 I/O Equivalent Circuits changed</p> <p>P13 initial value of INn added</p> <p>P15 add note to SPI RST_B sequence</p> <p>P16 SPI timing chart and add note changed</p> <p>P17 DIR (direct) mode timing chart (1) and note changed</p> <p>P18 Figure 26. and note changed</p> <p>P18 Figure 27. changed</p> <p>P19 timing chart of ① Overcurrent protection and ② Overheat protection changed explanation of error flag release changed</p> <p>P20 ③ Open detection changed</p> <p>P22 "7) Operation Under Strong Electromagnetic Field" added</p> <p>P23 "15) FIN" deleted</p> <p>Whole page all unit changed to SI unit</p>
08.Jun.2017	004	<p>P4 Max value of PWM Output range was changed from 5kHz to 1.2kHz.</p> <p>P4 "DIR=5V" was removed at Condition of PWM Output range.</p>

Notice

Precaution on using ROHM Products

1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment ^(Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASS III	CLASS III	CLASS II b	CLASS III
CLASS IV		CLASS III	

2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
 - [a] Installation of protection circuits or other protective devices to improve system safety
 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
3. Our Products are not designed under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc. prior to use, must be necessary:
 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
4. The Products are not subject to radiation-proof design.
5. Please verify and confirm characteristics of the final or mounted products in using the Products.
6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
8. Confirm that operation temperature is within the specified range described in the product specification.
9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification